

CMOS Hex Inverter

High-Voltage Types (20-Volt Rating)

■ CD4069UB types consist of six CMOS inverter circuits. These devices are intended for all general-purpose inverter applications where the medium-power TTL-drive and logic-level-conversion capabilities of circuits such as the CD4009 and CD4049 Hex Inverter/Buffers are not required.

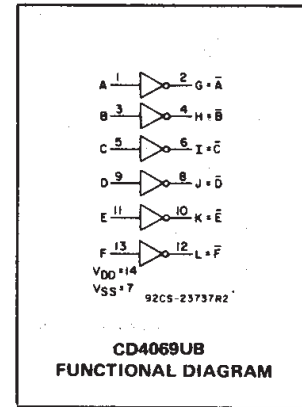
The CD4069UB-Series types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic package (E suffix), and in chip form (H suffix).

Features:

- Standardized symmetrical output characteristics
- Medium Speed Operation— $t_{PHL}, t_{PLH}=30$ ns (typ.) at 10 V
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μ A at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- Logic inversion
- Pulse shaping
- Oscillators
- High-input-impedance amplifiers



RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	Min.	Max.	
Supply Voltage Range (For T_A = Full Package Temperature Range)	3	18	V

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})	
Voltages referenced to V_{SS} Terminal -0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS -0.5V to $V_{DD} + 0.5V$
DC INPUT CURRENT, ANY ONE INPUT ± 10 mA
POWER DISSIPATION PER PACKAGE (P_D):	
For $T_A = -55^\circ\text{C}$ to $+100^\circ\text{C}$ 500 mW
For $T_A = +100^\circ\text{C}$ to $+125^\circ\text{C}$ Derate Linearly at 12 mW/°C to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR $T_A =$ FULL PACKAGE-TEMPERATURE RANGE (All Package Types) 100 mW
OPERATING-TEMPERATURE RANGE (T_A) -55°C to $+125^\circ\text{C}$
STORAGE TEMPERATURE RANGE (T_{stg}) -65°C to $+150^\circ\text{C}$
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 inch (1.59 \pm 0.79 mm) from case for 10s max $+265^\circ\text{C}$

DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$; Input $t_r, t_f = 20$ ns,

$C_L = 50$ pF, $R_L = 200$ K Ω

CHARACTERISTIC	CONDITIONS	LIMITS		UNITS	
		V_{DD} V	Typ.		Max.
Propagation Delay Time; t_{PLH}, t_{PHL}	$V_{DD} = 5$	55	110	ns	
	$V_{DD} = 10$	30	60		
	$V_{DD} = 15$	25	50		
Transition Time; t_{THL}, t_{TLH}	$V_{DD} = 5$	100	200	ns	
	$V_{DD} = 10$	50	100		
	$V_{DD} = 15$	40	80		
Input Capacitance; C_{IN}	Any Input	10	15	pF	

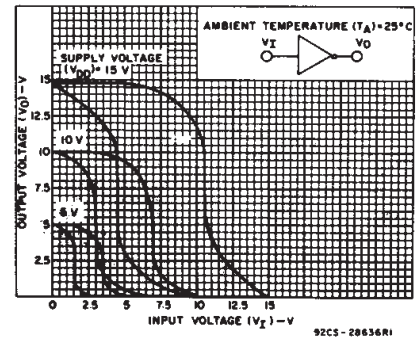


Fig. 1 — Minimum and maximum voltage transfer characteristics.

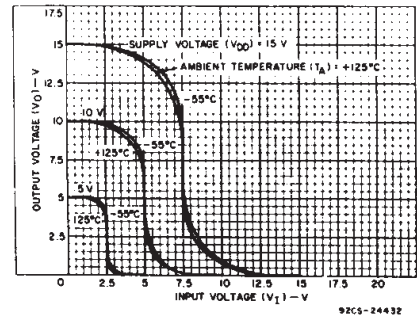


Fig. 2 — Typical voltage transfer characteristics as a function of temperature.

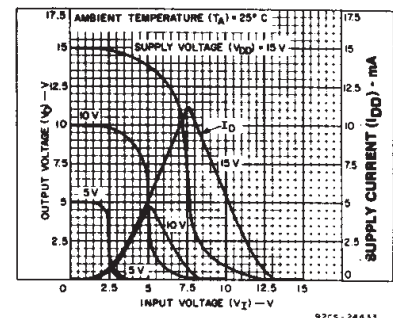


Fig. 3 — Typical current and voltage transfer characteristics.

CD4069UB Types

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)	-55	-40	+85	+125	+25			
								Min.	Typ.	Max.	
Quiescent Device Current, I _{DD} Max.	-	0,5	5	0.25	0.25	7.5	7.5	-	0.01	0.25	μA
	-	0,10	10	0.5	0.5	15	15	-	0.01	0.5	
	-	0,15	15	1	1	30	30	-	0.01	1	
	-	0,20	20	5	5	150	150	-	0.02	5	
Output Low (Sink) Current I _{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	-	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	-	
Output High (Source) Current, I _{OH} Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	-	mA
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-	
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-	
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-	
Output Voltage: Low-Level, V _{OL} Max.	-	5	5	0.05			-	0	0.05	-	V
	-	10	10	0.05			-	0	0.05	-	
	-	15	15	0.05			-	0	0.05	-	
Output Voltage: High-Level, V _{OH} Min.	-	0	5	4.95			4.95	5	-	-	V
	-	0	10	9.95			9.95	10	-	-	
	-	0	15	14.95			14.95	15	-	-	
Input Low Voltage, V _{IL} Max.	4.5	-	5	1			-	-	1	-	V
	9	-	10	2			-	-	2	-	
	13.5	-	15	2.5			-	-	2.5	-	
Input High Voltage, V _{IH} Min.	0.5	-	5	4			4	-	-	-	V
	1	-	10	8			8	-	-	-	
	1.5	-	15	12.5			12.5	-	-	-	
Input Current I _{IN} Max.		0,18	18	±0.1	±0.1	±1	±1	-	±10 ⁻⁵	±0.1	μA

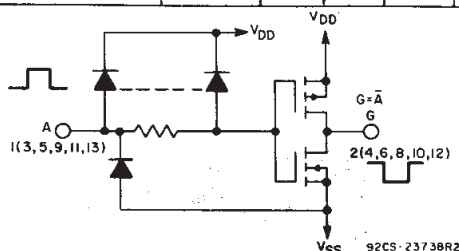


Fig. 6 - Schematic diagram of one of six identical inverters.

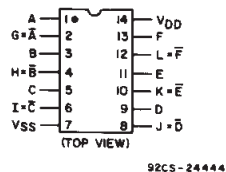


Fig. 7 - CD4069UB terminal assignment.

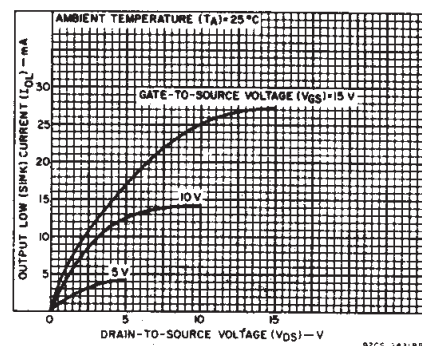


Fig. 4 - Typical output low (sink) current characteristics.

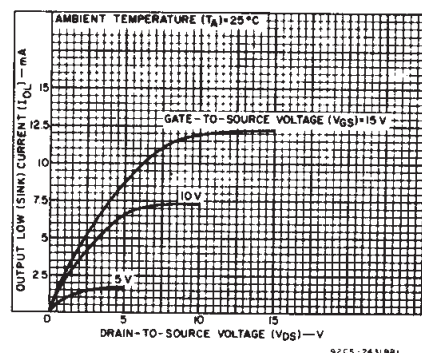


Fig. 5 - Minimum output low (sink) current characteristics.

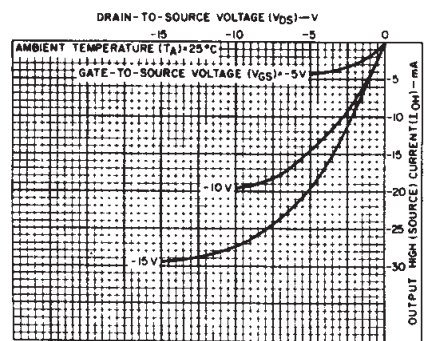


Fig. 8 - Typical output high (source) current characteristics.

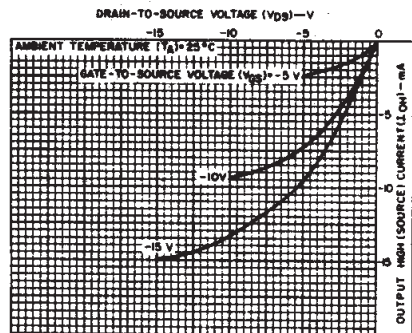


Fig. 9 - Minimum output high (source) current characteristics.

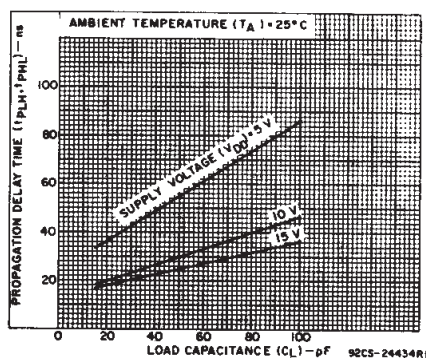


Fig. 10 - Typical propagation delay time vs. load capacitance.

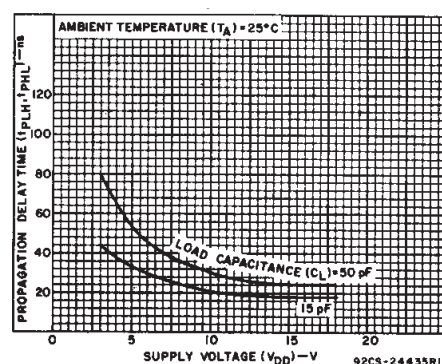


Fig. 11 - Typical propagation delay time vs. supply voltage.

3
COMMERCIAL CMOS
HIGH VOLTAGE ICs

CD4069UB Types

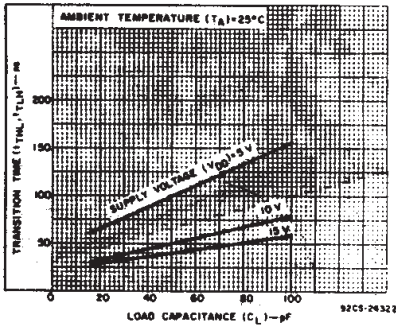


Fig. 12 - Typical transition time vs. load capacitance.

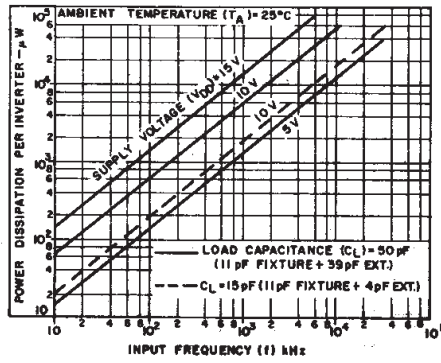


Fig. 13 - Typical dynamic power dissipation vs. frequency.

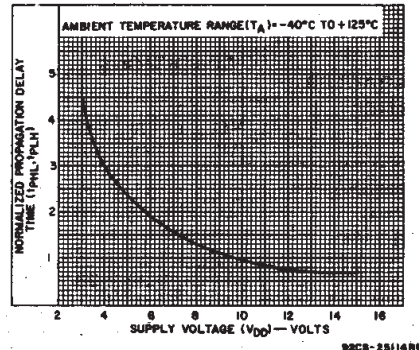


Fig. 14 - Variation of normalized propagation delay time (t_{PHL} and t_{PLH}) with supply voltage.

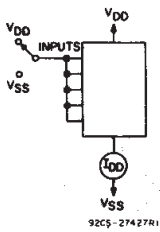


Fig. 15 - Quiescent device current test circuit.

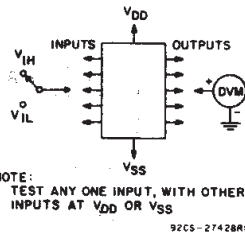


Fig. 16 - Noise immunity test circuit.

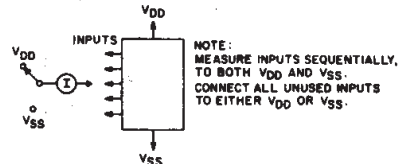


Fig. 17 - Input leakage current test circuit.

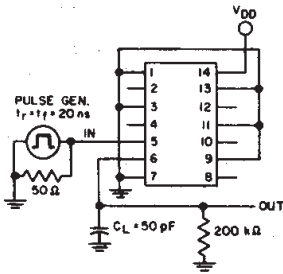
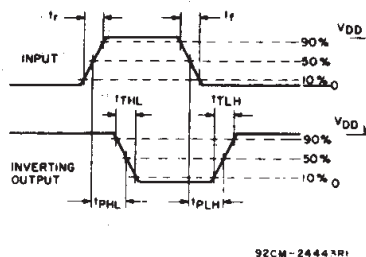


Fig. 18 - Dynamic electrical characteristics test circuit and waveforms.



92CM-24443R1

APPLICATIONS

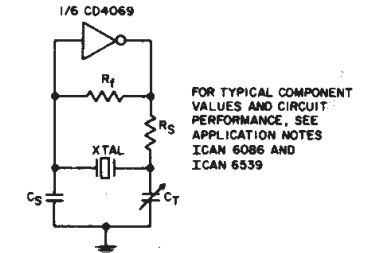


Fig. 19 - Typical crystal oscillator circuit.

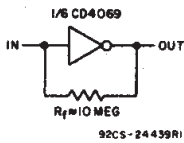


Fig. 20 - High-input impedance amplifier.

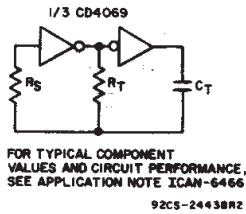


Fig. 21 - Typical RC oscillator circuit.

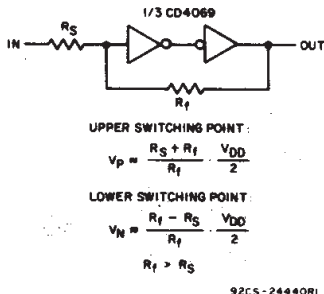


Fig. 22 - Input pulse shaping circuit (Schmitt trigger).

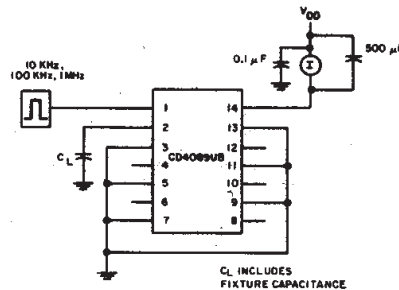
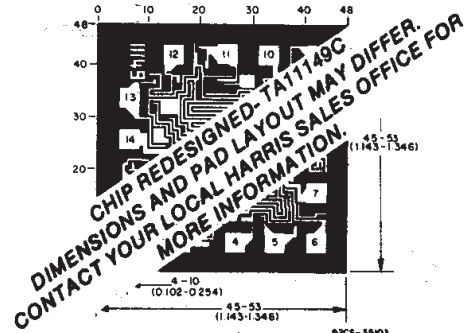


Fig. 23 - Dynamic power dissipation test circuit.



Dimensions and pad layout for CD4069UBH.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10⁻³ inch).

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.